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(54) **Field emission device and method for making same**

Feldemissionsvorrichtung und Verfahren zur Herstellung

Dispositif à émission de champ et procédé de fabrication

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WO-A-94/28569 **US-A- 5 312 514**

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Description**Field of the Invention**

[0001] This invention pertains to field emission devices and, in particular, to economical field emission devices particularly useful in displays.

Background of the Invention

[0002] A field emission device emits electrons in response to an applied electrostatic field. Such devices are useful in a wide variety of applications including displays, electron guns and electron beam lithography. A particularly promising application is the use of field emission devices in addressable arrays to make flat panel displays. See, for instance, the December 1991 issue of *Semiconductor International*, p. 11. C. A. Spindt et al., *IEEE Transactions on Electron Devices*, Vol. 38(10), pp. 2355-2363 (1991), and J.A. Castellano, *Handbook of Display Technology*, Academic Press, New York, pp. 254-257, (1992).

[0003] Conventional electron emission flat panel displays typically comprise a flat vacuum cell having a matrix array of microscopic field emitter cathode tips formed on one plate of the cell ("the back-plate") and a phosphor-coated anode on a transparent front plate. Between cathode and anode is a conductive element called a "grid" or "gate". The cathodes and gates are typically perpendicular strips whose intersections define pixels for the display. A given pixel is activated by applying voltage between the cathode conductor strip and the gate conductor strip whose intersection defines the pixel. A more positive voltage is applied to the anode in order to impart a relatively high energy (about 1000 eV) to the emitted electrons. See, for example, United States Patent Nos. 4,940,916; 5,129,850; 5,138,237; and 5,283,500.

[0004] A difficulty with these conventional flat panel displays is that they are difficult and expensive to make. In conventional approaches the gate conductors typically have important micron or submicron features which require expensive, state-of-the-art lithography. Accordingly, there is a need for an improved electron emission apparatus which can be economically manufactured for use in flat panel displays.

[0005] According to the present invention, there is provided a method as defined in claim 1 or 21, or a device as defined in claim 11, or 19.

[0006] A field emission device is made by disposing emitter material on an insulating substrate, applying masking particles to the emitter material, applying an insulating film and a gate conductor film over the masking particles and emitter material and removing the particles to reveal a random distribution of apertures to the emitter material. The result is a novel and economical field emission device having numerous randomly distributed emission apertures which can be used to make low cost

flat panel displays.

Brief Description of the Drawings

[0007] In the drawings:

FIG. 1 is a flow diagram of an improved process for making a field emission device;

FIGs. 2-4 are schematic cross sections of a field emission device at various stages of fabrication;

FIG. 5 shows an alternative embodiment of the FIG. 4 structure;

FIGs. 6 and 7 are scanning electron micrographs illustrating the masking effect of particles useful in the process of FIG. 1;

FIG. 8 is a cross sectional view of a flat panel display using a field emission device made by the process of FIG. 1; and

FIG. 9 is a schematic top view of the field emission device used in the display of FIG. 8.

Detailed Description

[0008] Referring to the drawings, FIG. 1 is a schematic flow diagram of an improved process for making a field emission device. The first step, shown in block A, is to provide a substrate. The substrate can be an insulating material or a conductively coating insulated material depending on whether the electron emitting material is conductive or not. If the finished device is intended for use in a display, the substrate preferably comprises a material such as glass, ceramic or silicon that can be joined with other materials to form a vacuum-sealed structure. Alternatively, an additional glass backplate can be placed underneath the substrate for sealing.

[0009] The next step shown in block B of FIG. 1 is to apply to the substrate a layer of emitter material. Advantageously, the emitter material is applied in a desired pattern. An emitter material is a conductive or semiconductive material having many points, such as sharp peaks, for field-induced emission of electrons. The peaks can be defined by known etching techniques or can be the result of embedding sharp emitter bodies in a matrix.

[0010] The emitter material can be chosen from a number of different materials that can emit electrons at relatively low applied electric fields, typically less than 50 volts/micron of distance between the emitter and the gate electrode, preferably less than 25 V/ μ m so that the industrially desirable CMOS type circuit drive can be used and even more preferably, less than 15 V/ μ m. Exemplary materials suitable as emitters include diamonds (either chemical vapor deposited, natural diamond grits, or synthetic diamonds, doped or undoped), graphite, metals such as Mo, W, Cs, compounds such as LaB₆, YB₆, AlN, or combinations of these materials and other low work function materials deposited as a film. Desirable emitter geometry includes sharp-tipped,

jagged, flaky or polyhedral shape, either periodically arranged or randomly distributed, so that the field concentration at the sharp tips can be utilized for low voltage operation of electron emission. Since multiple emitting points are desired for each pixel, a continuous film or layer of material with multiple sharp points or a multiplicity of polyhedral particles can be used. Materials with negative or low electron affinity, such as some n-type diamonds, emit electrons relatively easily at low applied voltages and thus may not require sharp tips for field concentration.

[0011] Since an electrical current must flow to the emitter point of the emitter bodies, it may be desired as a preliminary step to apply a conductive layer to the substrate and pattern it for contacting the emitter material. Preferably, however, the emitter material itself is made conductive as by mixing emitter bodies in a conductive slurry or paste such as silver-epoxy, low-melting point solder, or mixture of conductive metal particles. Particles of low-melting point glass can be added to promote heat-induced adhesion, and particles of easily reduced oxides, such as copper oxide, can be added to provide the glass with conductivity upon reduction in hydrogen. The conductive particle volume should exceed the percolation limit and is advantageously at least 30% and preferably at least 45%.

[0012] In the preferred approach, the layer of emitter material is applied to the substrate in a desired pattern by applying a conductive paste of the emitter material by screen printing or spray coating through a mask. Typically the desired pattern will be a series of parallel stripes. After application and patterning, the layer is dried, baked and, if desired, subjected to hydrogen or forming gas heat treatment to enhance conductivity. Alternatively, the layer can be applied as a continuous layer, and, if patterning is desired, patterned using conventional photolithography.

[0013] The third step shown in block C of FIG. 1 is to apply to the emitter material, masking particles to be used in creating a perforated gate structure. The particles may be chosen from a number of materials such as metals (e.g., Al, Zn, Co, Ni), ceramics (e.g., Al_2O_3 , MgO , NiO , BN), polymers (e.g., latex spheres) and composites. Typical desirable particle size is 0.1-100 μm , and preferably 0.3-10 μm . The particles may be spherical or randomly shaped. The particles are conveniently applied onto the surface of the emitter body by conventional particle dispensing techniques such as spray coating, spin coating or sprinkling. The particles may be mixed with volatile solvents such as acetone or alcohol for spray coating, with an optional addition of a small amount of organic binder material to improve adhesion on the emitter surface. After the volatile solvent dries off, a dielectric film and a gate conductor film are deposited, using the particles applied in step C as masks. The particles are then easily removed as by brushing off, with an artist's brush. Any residual binder material can be removed either by solvent or by heating. If ferromagnetic

particles such as Fe, Co, Ni, and their alloys or oxides such as ferrites, etc. are used as the mask particles, they can be removed by magnetic pull, reducing the risk of residual unremoved particles.

[0014] One particularly advantageous technique is to deposit the particles electrostatically. The particles can be dry sprayed from a nozzle at a high voltage. As they leave the nozzle, they will acquire an electric charge, and will thus repel one another, as well as being attracted to the emitter stripes. The mutual repulsion of the mask particles will produce a more uniform spacing across the emitter material, and thus allow a higher density of mask particles without exceeding the percolation limit and thus rendering the gate nonconductive. It is particularly advantageous to use dielectric mask particles, as they will retain some of their charge even after landing on the emitter material, and will thus force incoming particles into areas with a low density of previous mask particles.

[0015] As an additional refinement, the emitter electrodes may be charged to the opposite polarity from the mask particles, and the exposed substrate in between emitter electrodes may be charged to the same polarity as the mask particles. Few particles will then land between the emitter electrodes, which will increase the average end-to-end conductivity of the gate, and allow a larger density of mask particles without rendering the gate nonconductive.

[0016] The resulting structure, shown in FIG. 2, comprises insulating substrate 10, emitter layer 11 and mask particles 12 randomly distributed on the emitter layer.

[0017] The next step shown in FIG. 1, block D, is to apply a dielectric film onto the emitter layer. The dielectric should be an electrically insulating material with a high breakdown voltage. Exemplary dielectric materials include SiO_2 , glass, single- or multi-component ceramics (including oxides and nitrides) and polymers such as polyamides. These films can be deposited by physical, chemical or electrochemical means. In the case of polymeric materials, care must be taken to avoid or minimize out-gassing of volatile components into the vacuum system in the field emission apparatus. The desired thickness of the dielectric film is typically 0.01-5 μm , and preferably 0.05-1 μm to ensure the needed electrical insulation during the voltage application while maximizing the electron accelerating effect by the proximity of the gate electrode to the emitter body.

[0018] The fifth step (block E) is to apply a film of gate conductor material over the dielectric to act as a gate conductor. The gate conductor material is typically chosen from metals such as Cu, Cr, Ni, Nb, Mo, W or alloys thereof, but the use of highly conductive non-metallic compounds such as oxides (e.g., Y-Ba-Cu-O, La-Ca-Mn-O), nitrides, carbides is not prohibited. The desirable thickness of the gate conductor is 0.05-10 μm and preferably 0.2-5 μm . The resulting structure is shown in FIG. 3 wherein dielectric film 30 and gate conductor film 31 have successively been applied over the structure of

FIG. 2. The mask particles 12 protect the underlying regions of emitter material 11. The gate conductor film 31 is preferably formed into a pattern of stripes perpendicular to the stripes of the electron emitting layer 12. The regions of intersection between stripes of the emitter layer and stripes of the gate conductor layer will form an addressable array of electron sources.

[0019] The next step (block F) is to remove the mask particles, leaving apertures which expose the underlying emitter material. The mask particles can be removed by brushing, as with an artist's paint brush, to expose the virgin emitter surface beneath the particles. The resulting structure with exposed aperture portions 40 of the emitter layer 11 is shown in FIG. 4. Because of the random mask particle distribution, the resultant gate apertures also have random distribution rather than the typically periodic distribution as in photolithographically created gate apertures. The preferred size of the gate perforation is 0.1-50 μm , preferably 0.2-5 μm in diameter. The fraction of the perforation is desirably at least 5% and preferably at least 20% while remaining below the percolation threshold so that the gate remains continuous. A large number of gate apertures per pixel is desired for the sake of display uniformity. The number of the apertures is at least 50, and preferably at least 200 per pixel.

[0020] FIG. 5 illustrates an alternative form of the structure after step F where the emitter layer 11 is discontinuous (or non-conductive) and has been applied on a conductive layer 50 for providing current to the emitter points. The conductive layer can be applied to substrate 10 in a step preliminary to the application of emitter layer 11. The discontinuous emitter particles may be prepared by thin fiber processing such as a chemical vapor deposition or by screen printing or spray coating of electron emitting particles such as diamond or graphite.

[0021] Shown in FIGs. 6 and 7 are exemplary scanning electron microscopy (SEM) photomicrographs of the masked structure taken at a magnification of about X4500. Fine aluminum particles were mixed with acetone and spray coated on glass substrate and the solvent was allowed to dry off. The glass substrate partially covered with the mask particles was then coated with a 1 μm thick Cu film by thermal evaporation deposition using a Cu source. FIG. 6 shows the SEM micrograph of the substrate with the mask particles after the Cu film has been deposited. Because of the shadow effect, the areas of the substrate beneath the mask particles are not coated with the conductor. FIG. 7 shows that after gently brushing off the particles using an artist brush, only the holes (2-4 μm size) are left. Such fine-scale perforated metal layers are suitable as a multi-channel gate structure. Thus, a perforated gate structure with micron-level apertures is produced without using the costly photolithographic processing.

[0022] For display applications emitter material (the cold cathode) in each pixel of the display desirably con-

sists of multiple electron-emitting points for the purpose, among other things, of averaging out and ensuring uniformity in display quality. Since efficient electron emission at low applied voltages is typically achieved by the presence of the accelerating gate electrode in close proximity (typically about micron level distance), it is desirable to have multiple gate apertures over a given emitter body to maximally utilize the capability of multiple electron emission source. For example, each (100 μm) square pixel in a field emission device can contain as many as 2500 diamond island emitting points per pixel. It is desirable to have a fine-scale, micron-size gate structure with as many gate apertures as possible for maximum emission efficiency. Advantageously, the gate apertures have a diameter approximately equal to the emitter-gate spacing.

[0023] The final step is to complete the fabrication of the electron emitting device in the conventional fashion. This generally involves forming an anode and disposing it in spaced relation from the cold cathode emitting material within a vacuum seal. In the case of a flat panel display completion involves making the structure of FIG. 8 which shows an exemplary flat panel display using a device prepared by the process of FIG. 1.

[0024] Specifically, an anode conductor 80 formed on a transparent insulating substrate 81 is provided with a phosphor layer 82 and mounted on support pillars 83 in spaced relation from the device of FIG. 4 (or the device of FIG. 5). The space between the anode and the emitter is sealed and evacuated, and voltage is applied by power supply 84. The field-emitted electrons from the activated cold cathode electron emitters 11 are accelerated by the perforated gate electrode 31 from the multiple apertures 40 on each pixel and move toward the anode conductor layer 80 (typically transparent conductor such as indium-tin-oxide) coated on the anode substrate 81 (advantageously a glass face plate). Phosphor layer 82 is disposed between the electron emitter apparatus and the anode. As the accelerated electrons hit the phosphor, a display image is generated. The phosphor layer 82 can be deposited on the anode conductor 80 using the known TV screen technology.

[0025] FIG. 9 illustrates the columns 90 of the emitter array and the rows 91 of the gate conductor array to form an x-y matrix display in the device of FIG. 8. These rows and columns can be prepared by low-cost screen printing of emitter material (e.g., with 100 μm width), and physical vapor deposition of the gate conductor through a strip metal mask with a 100 μm wide parallel gaps. Depending on the activation voltage of a particular column of gate and a particular row of emitter, a specific pixel is selectively activated at the intersection of column and row to emit electrons and activate the phosphor display screen above that pixel.

[0026] In addition to the simplicity, low cost, and reduced environmental wastes associated with the elimination of fine-line lithography, the particle-mask technique of FIG. 1 offers an advantage of providing confor-

mal deposition of dielectric and gate conductor films regardless of the real-life variations in emitter height or width. For example, the emitter body may be constructed by a low-cost, screen-printing or spray-coating process using a mixture of diamond particles (for field emission), metal or conductive particles (for conducting electricity), glass frits (for partial or complete melting for adhesion to the glass backplate), organic binder (for viscosity control during screen printing) and solvent (for dissolution of the binder). If the screen printed and cured emitter strips have a dimension of 50 μm height and 100 μm width, it is reasonable to anticipate a dimensional variation of at least 1-5 μm , e.g., in height. In view of the desirable gate-emitter distance of about 1 μm level or smaller, such a height variation in emitter is not acceptable from the product reliability aspect unless the gate structure can be made conformal and maintains the 1 μm level distance.

[0027] The process of creating the micron-level, perforated gate structure described above is only an example of many possible variations in processing, structure, and configuration. For example, either the dielectric film or the gate conductor film can be selectively chemically etched, to provide greater exposure of the other unetched material. In another example, the deposition of dielectric film and the gate conductor film over the mask particles can be repeated more than once to create multi-layered gate apertures for the purpose of shaping the trajectories of the emitted electron beam or for triode operation. Yet in another example, the mask particles can be applied after the dielectric and the conductor films in Fig. 3 are already deposited, and then a layer of etch-blocking mask material (polymeric or inorganic material that are resistance to acid) can be deposited over the mask particles by evaporation or spray coating. The mask particles are brushed away leaving apertures in the etch-blocking layer and thereby defining an etch mask. The regions not covered by the etch-blocking mask layer are then etched away e.g., the metallic gate conductor film such as Cr can be etched with nitric acid and the dielectric film such as glass with hydrofluoric acid to create the gate apertures and expose the underlying emitter material. The etch-blocking mask is then removed, e.g., by solvent.

[0028] The apparatus can also be useful for a variety of devices including flat panel display, electron beam guns, microwave power amplifier tubes, ion source, and as a matrix-addressable source for electrons for electron-lithography. (See, P.W. Hawkes, "Advances in Electronics and Electron Physics", Academic Press, New York, Vol. 83, pp. 75-85 and p. 107, (1992). In the latter device, the activation of selected rows and columns would provide emitted electrons from specific, predetermined pixels, thus achieving selective etching of electron-sensitive lithography resist material (such as polymethyl methacrylate (PMMA) for patterning, for example, of ultra high-density circuits. This feature is advantageous over the conventional electron beam lithog-

raphy apparatus which typically achieves pattern writing using scanning procedure and hence the throughput is much less, as described in "VLSI Technology" by S.M. Sze, McGraw Hill, New York, 1988, p. 155 and p. 165.

[0029] The apparatus, when used as matrix addressable ion source apparatus, emits electrons from activated pixel areas which impact ambient gas molecules and cause ionization.

Claims

1. A method for making a field emission device comprising the steps of:
 - applying a layer of electron emitter material (11) on a substrate (10);
 - applying masking particles (12) to said emitter material;
 - applying over said masking particles and said emitter material successive layers of insulating material (30) and conductive material (31), said layers of insulating material and conductive material containing a random distribution of apertures (40) to said electron emitter material;
 - removing said masking particles to reveal underlying apertures to the emitter material; and
 - finishing said device.
2. The method of claim 1 further comprising the step of applying a conductive layer (50) to said substrate before the step of applying said electron emitter material.
3. The method of claim 1 wherein said layer of electron emitter material is applied by applying a conductive slurry including electron emitting material.
4. The method of claim 1 wherein said masking particles are applied electrostatically.
5. The method of claim 1 wherein said masking particles have particle size in the range 0.1 to 100 micrometers.
6. The method of claim 1 wherein said masking particles are moved by brushing.
7. The method of claim 1 wherein said masking particles are magnetic and are removed by magnetic pulling.
8. The method of claim 1 including the step of patterning said layer of electron emitter material.
9. The method of claim 1 including the step of patterning said layer of conductive material.

10. The method of claim 1 including the step of patterning said layer of electron emitter material into a series of parallel stripes and the step of patterning said layer of conductive material into a second series of parallel stripes intersecting said first series of stripes. 5
11. A field emission device comprising:
 a substrate supported layer of electron emitting material (11);
 means (50) for electrically contacting said layer of electron emitting material;
 successive layers of dielectric (30) and conductive (31) material overlying said electron emitting material, said layers containing a random distribution of apertures (40) to said electron emitting material. 10 15
12. A field emission device according to claim 11 wherein said dielectric layer has a thickness in the range 0.01 to 5 micrometers. 20
13. A field emission device according to claim 11 wherein said conductor layer has a thickness in the range 0.2 to 5 micrometers. 25
14. A field emission device according to claim 11 wherein said apertures form perforations in the conductive layer predominantly in the range 0.1 to 50 micrometers in diameter. 30
15. A field emission device according to claim 11 wherein said apertures form a perforation fraction in the conductive layer of at least 5% but remaining below the percolation threshold. 35
16. A field emission device according to claim 11 wherein said electron emitting material is a material selected from the group consisting of diamond, graphite, Mo, W, Cs, $L_a B_6$, YB_6 , or AlN. 40
17. A field emission device according to claim 11 wherein said layer of electron emitting material and said layer of conductive material are patterned to define a plurality of addressable intersecting regions. 45
18. A display device comprising a field emission device according to claim 11 or claim 12 or claim 13 or claim 14 or claim 15 or claim 16 or claim 17. 50
19. A flat panel display device of the type comprising a vacuum cell having an array of field emitter cathodes (11) on the back-plate (10) of the cell and a phosphor-coated anode (80) on a transparent front plate (81), one or more conductive gate layers (31) disposed between said anodes and said cathodes. said cathodes and gates formed into patterns for 55

defining pixels for the display, **characterised in that**

said gate layer comprises a random distribution of perforations predominantly in the range 0.1 to 50 micrometers in diameter for providing apertures (40) to said field emitter cathodes.

20. The flat panel display of claim 19 wherein the portion of the gate layer defining a pixel has at least 50 random perforations in the range 0.1 to 50 micrometers in diameter.
21. A method for making a field emission device comprising the steps of applying a layer of electron emitting material (11) on a substrate (10), applying over said emitting material a layer of insulating material (30) and a layer of conductive material (31), and forming apertures (40) through the conductive material and the insulating material to the electron emitting material, **characterised in that** said step of forming apertures comprises the application of masking particles (12) to the surface of the workpiece to a random distribution of apertures and the removal of said masking particles to reveal underlying apertures to the electron emitting material.
22. The method of claim 21 wherein said masking particles are applied to the emitter material prior to the application of said insulating layer.
23. The method of claim 21 wherein said masking particles are applied to said conductive material prior to the application of a subsequent etch blocking layer to act as an etching mask.

Patentansprüche

1. Verfahren zur Herstellung eines Feldemissionsbauelements, mit den folgenden Schritten:
- Auftragen einer Schicht aus Elektronenemittermaterial (11) auf ein Substrat (10);
 Auftragen von maskierenden Teilchen (12) auf das Emittiermaterial;
 Auftragen von aufeinanderfolgenden Schichten aus Isoliermaterial (30) und leitendem Material (31) über den maskierenden Teilchen und dem Emittiermaterial, wobei die Schichten aus Isoliermaterial und leitendem Material eine Zufallsverteilung von Öffnungen (40) zu dem Elektronenemittermaterial enthalten;
 Entfernen der maskierenden Teilchen, um darunterliegende Öffnungen zu dem Emittiermaterial freizulegen; und
 Fertigstellen des Bauelements.
2. Verfahren nach Anspruch 1, weiterhin mit dem

Schritt des Auftragens einer leitenden Schicht (50) auf das Substrat vor dem Schritt des Auftragens des Elektronenemittermaterials.

3. Verfahren nach Anspruch 1, bei dem die Schicht aus Elektronenemittermaterial aufgetragen wird, indem eine Elektronen emittierendes Material enthaltende leitende Aufschlammung aufgetragen wird. 5
4. Verfahren nach Anspruch 1, bei dem die maskierenden Teilchen elektrostatisch aufgetragen werden. 10
5. Verfahren nach Anspruch 1, bei dem die Teilchengröße der maskierenden Teilchen im Bereich von 0,1 bis 100 Mikrometern liegt. 15
6. Verfahren nach Anspruch 1, bei dem die maskierenden Teilchen durch Bürsten bewegt werden. 20
7. Verfahren nach Anspruch 1, bei dem die maskierenden Teilchen magnetisch sind und durch magnetisches Ziehen entfernt werden. 25
8. Verfahren nach Anspruch 1 mit dem Schritt des Strukturierens der Schicht aus Elektronenemittermaterial. 30
9. Verfahren nach Anspruch 1 mit dem Schritt des Strukturierens der Schicht aus leitendem Material. 35
10. Verfahren nach Anspruch 1 mit dem Schritt des Strukturierens der Schicht aus Elektronenemittermaterial zu einer Reihe paralleler Streifen und dem Schritt des Strukturierens der Schicht aus leitendem Material zu einer die erste Reihe von Streifen schneidenden zweiten Reihe paralleler Streifen. 40
11. Feldemissionsbauelement, das folgendes umfaßt: 45
 - eine von einem Substrat gestützte Schicht aus Elektronen emittierendem Material (11);
 - aufeinanderfolgende Schichten aus dielektrischem (30) und leitendem (31) Material, die über dem Elektronen emittierenden Material liegen, wobei die Schichten eine Zufallsverteilung von Öffnungen (40) zu dem Elektronen emittierenden Material enthalten.
12. Feldemissionsbauelement nach Anspruch 11, bei dem die Dicke der dielektrischen Schicht im Bereich von 0,01 bis 5 Mikrometern liegt. 50
13. Feldemissionsbauelement nach Anspruch 11, bei dem die Dicke der Leiterschicht im Bereich von 0,2 bis 5 Mikrometern liegt. 55
14. Feldemissionsbauelement nach Anspruch 11, bei dem die Öffnungen Perforationen in der leitenden Schicht mit einem Durchmesser bilden, der hauptsächlich im Bereich von 0,1 bis 50 Mikrometern liegt.
15. Feldemissionsbauelement nach Anspruch 11, bei dem die Öffnungen in der leitenden Schicht einen Perforationsanteil von mindestens 5% bilden, der aber unter dem Perkolationsschwellwert bleibt.
16. Feldemissionsbauelement nach Anspruch 11, bei dem das Elektronen emittierende Material ein aus der Gruppe bestehend aus Diamant, Graphit, Mo, W, Cs, $L_a B_6$, YB_6 oder AlN ausgewähltes Material ist.
17. Feldemissionsbauelement nach Anspruch 11, bei dem die Schicht aus Elektronen emittierendem Material und die Schicht aus leitendem Material so strukturiert sind, daß sie mehrere adressierbare, sich schneidende Gebiete definieren.
18. Anzeigebauelement, das ein Feldemissionsbauelement nach Anspruch 11 oder Anspruch 12 oder Anspruch 13 oder Anspruch 14 oder Anspruch 15 oder Anspruch 16 oder Anspruch 17 umfaßt.
19. Flachbildschirm-Bauelement der Art, die folgendes umfaßt: eine Vakuumzelle mit einem Array von Feldemitterkathoden (11) auf der Gegenkathode (10) der Zelle und eine leuchtstoffbeschichtete Anode (80) auf einer transparenten Frontplatte (81), eine oder mehrere, zwischen den Anoden und den Kathoden angeordnete leitende Gateschichten (31), wobei die Kathoden und die Gates zu Mustern ausgebildet sind, um Pixel für das Display zu definieren, **dadurch gekennzeichnet, daß** die Gateschicht eine Zufallsverteilung von Perforationen mit einem Durchmesser umfaßt, der hauptsächlich im Bereich von 0,1 bis 50 Mikrometern liegt, um Öffnungen (40) zu den Feldemitterkathoden zu bilden.
20. Flachbildschirm nach Anspruch 19, bei dem derjenige Teil der Gateschicht, der ein Pixel definiert, mindestens 50 zufällige Perforationen mit einem Durchmesser aufweist, der im Bereich von 0,1 bis 50 Mikrometern liegt.
21. Verfahren zur Herstellung eines Feldemissionsbauelements, mit den folgenden Schritten: Auftragen einer Schicht aus Elektronen emittierendem Material (11) auf ein Substrat (10), Auftragen einer Schicht aus Isoliermaterial (30) und einer Schicht aus leitendem Material (31) über dem emittierenden Material und Ausbilden von Öffnungen (40) durch das leitende Material und das Isoliermaterial zu dem Elektronen emittierenden Material, **da-**

durch gekennzeichnet, daß der Schritt des Ausbildens von Öffnungen das Auftragen von maskierenden Teilchen (12) auf die Oberfläche des Werkstücks zu einer Zufallsverteilung von Öffnungen und das Entfernen der maskierenden Teilchen, um darunterliegende Öffnungen zu dem Elektronen emittierenden Material freizulegen, umfaßt.

22. Verfahren nach Anspruch 21, bei dem die maskierenden Teilchen vor dem Auftragen der Isolierschicht auf das Emittiermaterial aufgetragen werden.

23. Verfahren nach Anspruch 21, bei dem die maskierenden Teilchen vor dem Auftragen einer nachfolgenden, das Ätzen blockierenden Schicht aufgetragen werden, um wie eine Ätzmaske zu wirken.

Revendications

1. Procédé de fabrication d'un dispositif à émission de champ comprenant les étapes consistant :

à appliquer une couche d'un matériau émetteur d'électrons (11) sur un substrat (10);
à appliquer des particules de masquage (12) sur ledit matériau émetteur;
à appliquer sur lesdites particules de masquage et ledit matériau émetteur des couches successives de matériau isolant (30) et de matériau conducteur (31), lesdites couches de matériau isolant et de matériau conducteur contenant une distribution aléatoire d'ouvertures (40) vers ledit matériau émetteur d'électrons;
à retirer lesdites particules de masquage pour révéler les ouvertures sous-jacentes vers le matériau émetteur; et
à soumettre ledit dispositif à un traitement de finition.

2. Procédé selon la revendication 1, comprenant en outre l'étape d'application d'une couche conductrice (50) sur ledit substrat avant l'étape d'application dudit matériau émetteur d'électrons.

3. Procédé selon la revendication 1, dans lequel ladite couche de matériau émetteur d'électrons est appliquée en appliquant une suspension conductrice comprenant le matériau émetteur d'électrons.

4. Procédé selon la revendication 1, dans lequel lesdites particules de masquage sont appliquées par voie électrostatique.

5. Procédé selon la revendication 1, dans lequel lesdites particules de masquage ont une taille particulière dans la plage de 0,1 à 100 micromètres.

6. Procédé selon la revendication 1, dans lequel lesdites particules de masquage sont déplacées par brossage.

5 7. Procédé selon la revendication 1, dans lequel lesdites particules de masquage sont magnétiques et sont éliminées par attraction magnétique.

10 8. Procédé selon la revendication 1, comprenant l'étape de configuration de ladite couche de matériau émetteur d'électrons.

15 9. Procédé selon la revendication 1, comprenant l'étape de configuration de ladite couche de matériau conducteur.

20 10. Procédé selon la revendication 1, comprenant l'étape de configuration de ladite couche de matériau émetteur d'électrons en une série de bandes parallèles et l'étape de configuration de ladite couche de matériau conducteur en une seconde série de bandes parallèles coupant ladite première série de bandes.

25 11. Dispositif à émission de champ comprenant :

une couche de matériau émetteur d'électrons (11) posée sur un substrat;
un moyen (50) pour mettre en contact électrique ladite couche de matériau émetteur d'électrons;
des couches successives de matériau diélectrique (30) et de matériau conducteur (31) s'étendant sur ledit matériau émetteur d'électrons, lesdites couches contenant une distribution aléatoire d'ouvertures (40) vers ledit matériau émetteur d'électrons.

40 12. Appareil à émission de champ selon la revendication 11, dans lequel ladite couche diélectrique a une épaisseur dans la plage de 0,01 à 5 micromètres.

45 13. Appareil à émission de champ selon la revendication 11, dans lequel ladite couche conductrice a une épaisseur dans la plage de 0,2 à 5 micromètres.

50 14. Appareil à émission de champ selon la revendication 11, dans lequel lesdites ouvertures forment des perforations dans la couche conductrice de manière prédominante dans la plage de 0,1 à 50 micromètres de diamètre.

55 15. Appareil à émission de champ selon la revendication 11, dans lequel lesdites ouvertures forment une fraction de perforation dans la couche conductrice d'au moins 5%, mais restent en dessous du seuil de percolation.

16. Appareil à émission de champ selon la revendication 11, dans lequel ledit matériau émetteur d'électrons est un matériau choisi dans le groupe constitué du diamant, du graphite, de Mo, de W, de Cs, de L_aB_6 , de YB_6 ou de AlN. 5
17. Appareil à émission de champ selon la revendication 11, dans lequel ladite couche de matériau émetteur d'électrons et ladite couche de matériau conducteur sont configurées pour définir une pluralité de zones d'intersection adressables. 10
18. Dispositif d'affichage comprenant un appareil à émission de champ selon la revendication 11 ou 12 ou 13 ou 14 ou 15 ou 16 ou 17. 15
19. Dispositif d'affichage à panneau plat du type comprenant une cellule à vide ayant un réseau de cathodes émettrices de champ (11) sur la plaque arrière (10) de la cellule et une anode revêtue d'un matériau luminescent (80) sur une plaque avant transparente (81), une ou plusieurs couches de grille conductrices (31) disposées entre lesdites anodes et lesdites cathodes, lesdites cathodes et lesdites grilles étant formées en configurations pour définir des pixels pour l'affichage, **caractérisé en ce que** : 20
- ladite couche de grille comprend une distribution aléatoire de perforations de manière prédominante dans la plage de 0,1 à 50 micromètres de diamètre pour former des ouvertures (40) vers lesdites cathodes émettrices de champ. 25 30
20. Panneau d'affichage plat selon la revendication 19, dans lequel la partie de la couche de grille définissant un pixel a au moins 50 perforations aléatoires dans la plage de 0,1 à 50 micromètres de diamètre. 35
21. Procédé de fabrication d'un dispositif à émission de champ, comprenant les étapes consistant à appliquer une couche d'un matériau émetteur d'électrons (11) sur un substrat (10), à appliquer sur ledit matériau émetteur une couche de matériau isolant (30) et une couche de matériau conducteur (31), et à former des ouvertures (40) à travers le matériau conducteur et le matériau isolant vers le matériau émetteur d'électrons, **caractérisé en ce que** ladite étape de formation d'ouvertures comprend l'application de particules de masquage (12) à la surface de la pièce selon une distribution aléatoire d'ouvertures et le retrait desdites particules de masquage pour révéler les ouvertures sous-jacentes vers le matériau émetteur d'électrons. 40 45 50
22. Procédé selon la revendication 21, dans lequel lesdites particules de masquage sont appliquées au matériau émetteur avant l'application de ladite couche isolante. 55
23. Procédé selon la revendication 21, dans lequel lesdites particules de masquage sont appliquées audit matériau conducteur avant l'application d'une couche de blocage de gravure ultérieure pour agir comme masque de gravure.

FIG. 1

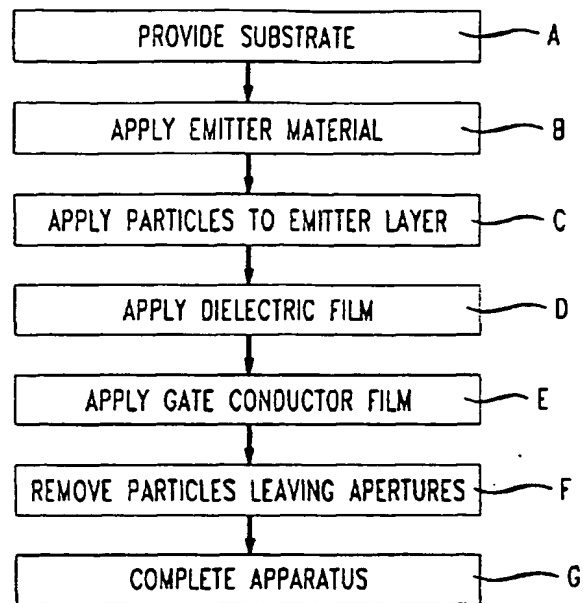


FIG. 2

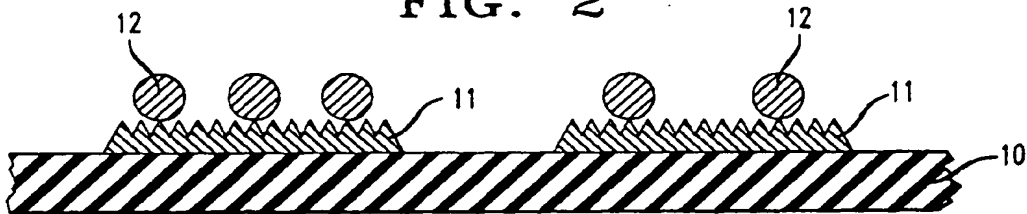


FIG. 3

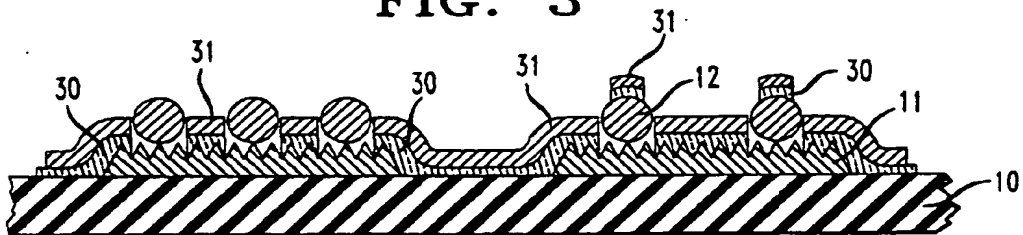


FIG. 4

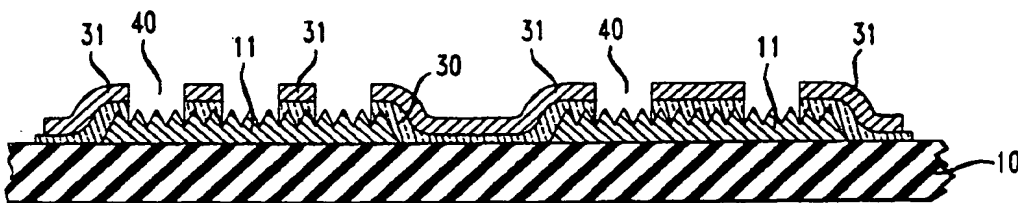


FIG. 5

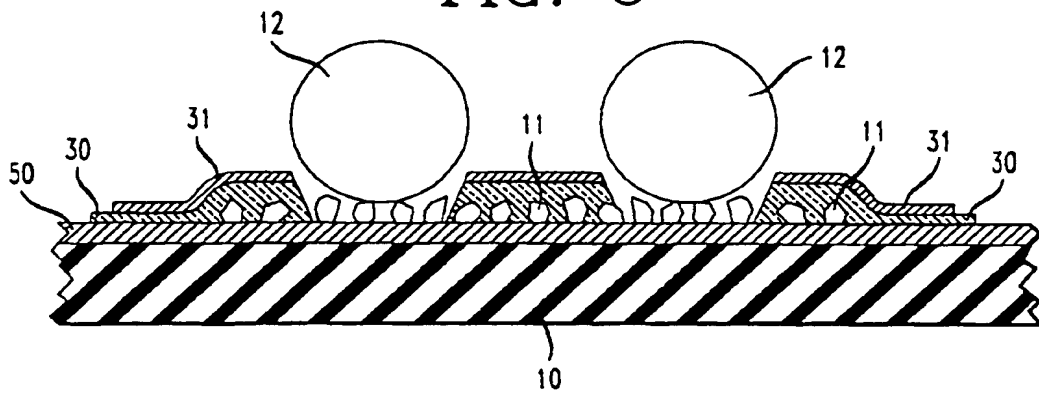


FIG. 8

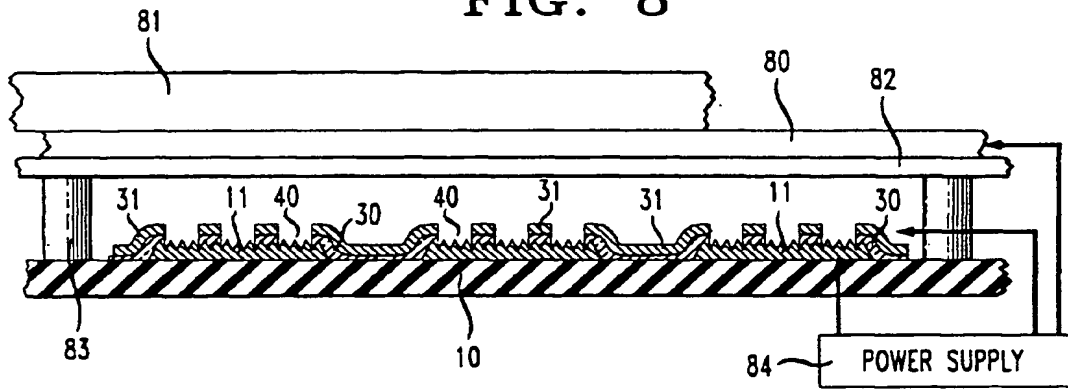


FIG. 9

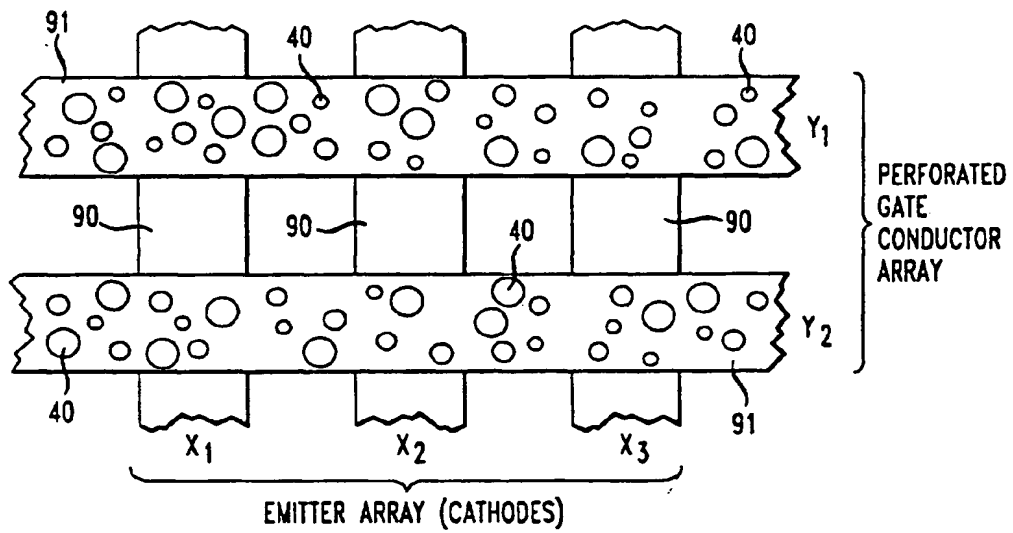
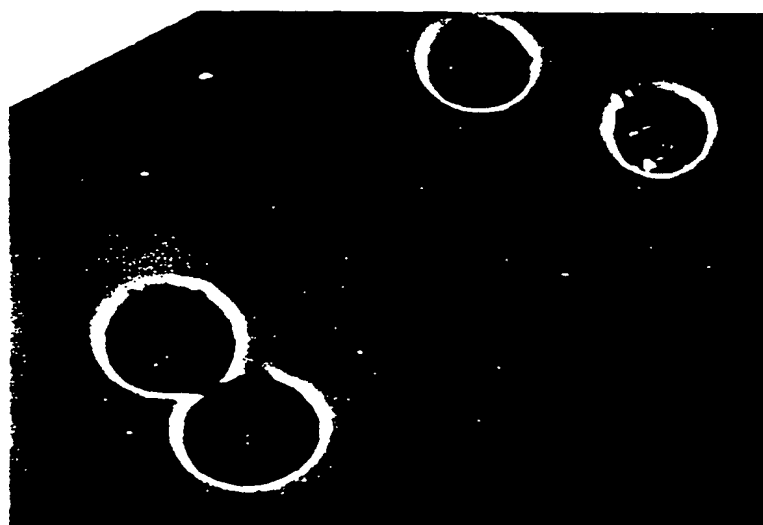


FIG. 6



FIG. 7



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